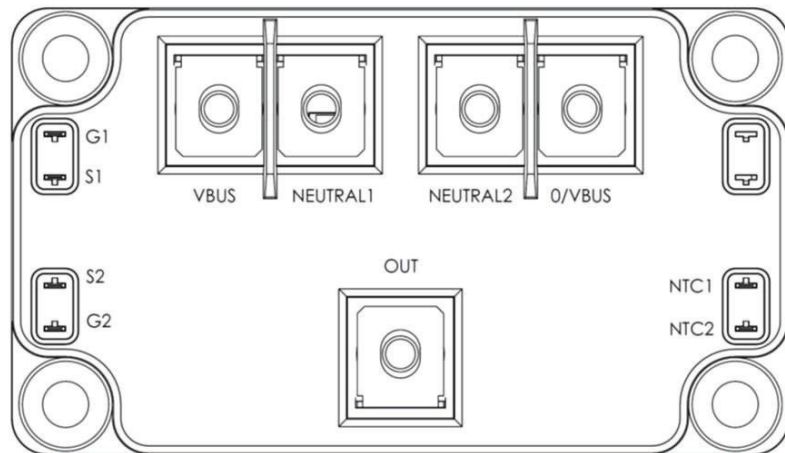
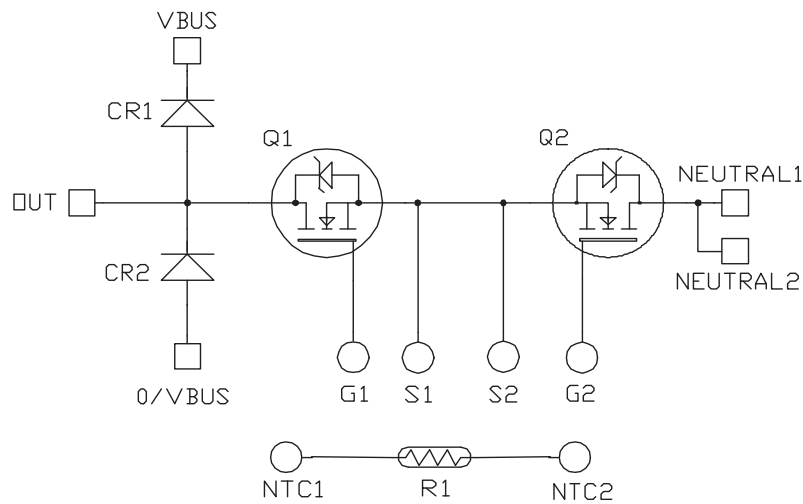


Vienna Rectifier SiC MOSFET Power Module

Product Overview

The MSCSM120VR1M062CT6AG device is a Vienna rectifier 1200V, 420A silicon carbide (SiC) power module.



Note: All ratings at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified.



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM120VR1M062CT6AG device:

- SiC Power MOSFET
 - Low $R_{DS(on)}$
 - High temperature performance
- SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on V_F
- Kelvin source for easy drive
- Low stray inductance
- M5 power connectors
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AlN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM120VR1M062CT6AG device:

- Outstanding performance at high frequency operation
- High-power and high-efficiency rectifiers and converters
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant

Applications

The following are the applications of MSCSM120VR1M062CT6AG device:

- Power factor correction
- Switched mode power supplies
- Uninterruptible power supplies

1. Electrical Specifications

The following sections show the electrical specifications of the MSCSM120VR1M062CT6AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the MSCSM120VR1M062CT6AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{DSS}	Drain-Source voltage	1200	V
I_D	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	420
		$T_C = 80\text{ }^\circ\text{C}$	334
I_{DM}	Pulsed drain current	840	
V_{GS}	Gate-Source voltage	-10/23	V
$R_{DS(on)}$	Drain-Source ON resistance	6.2	m Ω
P_D	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	1753

The following table lists the electrical characteristics (per SiC MOSFET) of the MSCSM120VR1M062CT6AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0V; V_{DS} = 1200V$	—	50	500	μA	
$R_{DS(on)}$	Drain-Source on resistance	$V_{GS} = 20V$ $I_D = 200A$	$T_J = 25\text{ }^\circ\text{C}$	—	5	6.2	m Ω
			$T_J = 175\text{ }^\circ\text{C}$	—	8	—	
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}; I_D = 15\text{ mA}$	1.8	2.8	—	V	
I_{GSS}	Gate-Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$	—	—	500	nA	

MSCSM120VR1M062CT6AG

Electrical Specifications

The following table lists the dynamic characteristics (per SiC MOSFET) of the MSCSM120VR1M062CT6AG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
C_{iss}	Input capacitance	$V_{GS} = 0V$	—	15.1	—	nF	
C_{oss}	Output capacitance	$V_{DS} = 1000V$	—	1.4	—		
C_{rss}	Reverse transfer capacitance	$f = 1\text{ MHz}$	—	0.13	—		
Q_g	Total gate charge	$V_{GS} = -5V/20V$	—	1160	—	nC	
Q_{gs}	Gate-source charge	$V_{Bus} = 800V$	—	205	—		
Q_{gd}	Gate-drain charge	$I_D = 200A$	—	250	—		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5V/20V$	—	56	—	ns	
T_r	Rise time	$V_{Bus} = 600V$	—	55	—		
$T_{d(off)}$	Turn-off delay time	$I_D = 250A$	—	166	—		
T_f	Fall time	$T_J = 150\text{ °C}$ $R_{GON} = 1.6\Omega$ $R_{GOFF} = 0.9\Omega$	—	67	—		
E_{on}	Turn-on energy	$V_{GS} = -5V/20V$	$T_J = 150\text{ °C}$	—	5	—	mJ
E_{off}	Turn-off energy	$V_{Bus} = 600V$ $I_D = 250A$ $R_{GON} = 1.6\Omega$ $R_{GOFF} = 0.9\Omega$	$T_J = 150\text{ °C}$	—	4.5	—	
R_{Gint}	Internal gate resistance		—	1.18	—	Ω	
R_{thJC}	Junction-to-case thermal resistance		—	—	0.086	$^{\circ}C/W$	

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the MSCSM120VR1M062CT6AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 200A$	—	4	—	V
		$V_{GS} = -5V; I_{SD} = 200A$	—	4.2	—	
t_{rr}	Reverse recovery time	$I_{SD} = 200A$	—	90	—	ns
Q_{rr}	Reverse recovery charge	$V_{GS} = -5V$	—	2750	—	nC
I_{rr}	Reverse recovery current	$V_R = 800V$ $di_f/dt = 5000\text{ A}/\mu s$	—	68	—	A

1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of the MSCSM120VR1M062CT6AG device.

Table 1-5. SiC Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
V_{RRM}	Peak repetitive reverse voltage		—	—	1700	V	
I_{RM}	Reverse leakage current	$V_R = 1700V$	$T_J = 25\text{ }^\circ\text{C}$	—	60	1200	μA
			$T_J = 175\text{ }^\circ\text{C}$	—	900	—	
I_F	Forward current						
V_F	Diode forward voltage	$I_F = 180A$	$T_J = 25\text{ }^\circ\text{C}$	—	1.5	1.8	V
			$T_J = 175\text{ }^\circ\text{C}$	—	2.3	—	
Q_C	Total capacitive charge	$V_R = 900V$	—	1380	—	nC	
C	Total capacitance	$f = 1\text{ MHz}, V_R = 600V$	—	1002	—	pF	
		$f = 1\text{ MHz}, V_R = 900V$	—	828	—		
R_{thJC}	Junction-to-case thermal resistance		—	—	0.1	$^\circ\text{C/W}$	

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120VR1M062CT6AG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic	Min.	Max.	Unit		
V _{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz	4000	—	V		
T _J	Operating junction temperature range	−40	175	°C		
T _{JOP}	Recommended junction temperature under switching conditions	−40	T _{Jmax} −25			
T _{STG}	Storage case temperature	−40	125			
T _C	Operating case temperature	−40	125			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight	—	300	g		

The following table lists the temperature sensor NTC of the MSCSM120VR1M062CT6AG device.

Table 1-7. Temperature Sensor NTC

Symbol	Characteristic	Min.	Typ.	Max.	Unit	
R ₂₅	Resistance at 25 °C	—	50	—	kΩ	
ΔR ₂₅ /R ₂₅	—	—	5	—	%	
B _{25/85}	T ₂₅ = 298.15K	—	3952	—	K	
ΔB/B	—	T _C = 100 °C	—	4	—	%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Note: See [APT0406—Using NTC Temperature Sensor Integrated into Power Module](#) for more information.

1.4 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM120VR1M062CT6AG device.

Figure 1-1. Maximum Thermal Impedance

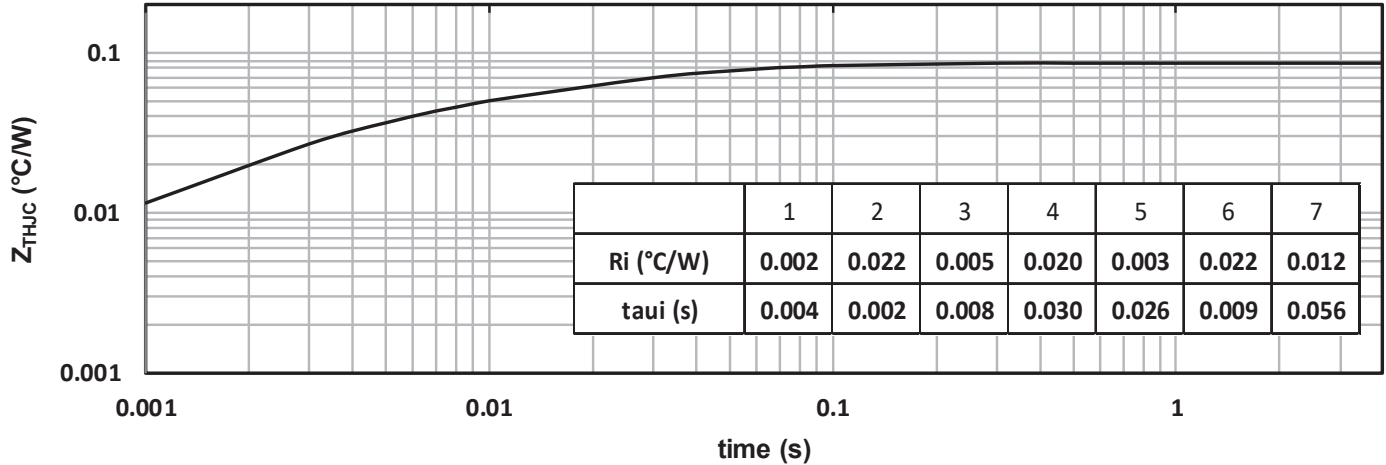


Figure 1-2. Output Characteristics, $T_J = 25\text{ }^\circ\text{C}$

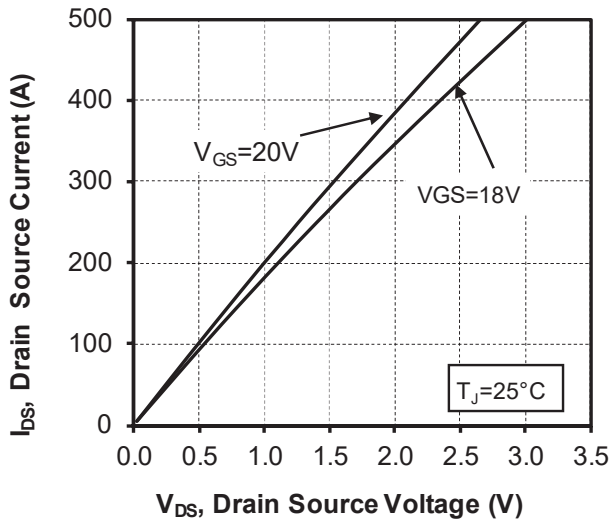
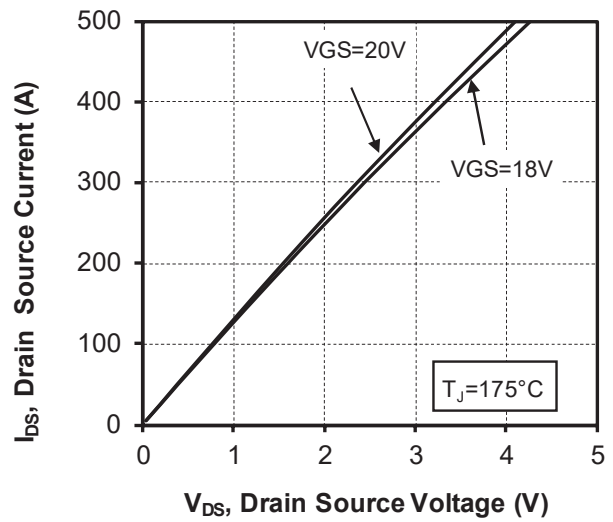


Figure 1-3. Output Characteristics, $T_J = 175\text{ }^\circ\text{C}$



MSCSM120VR1M062CT6AG

Electrical Specifications

Figure 1-4. Normalized $R_{DS(on)}$ vs. Temperature

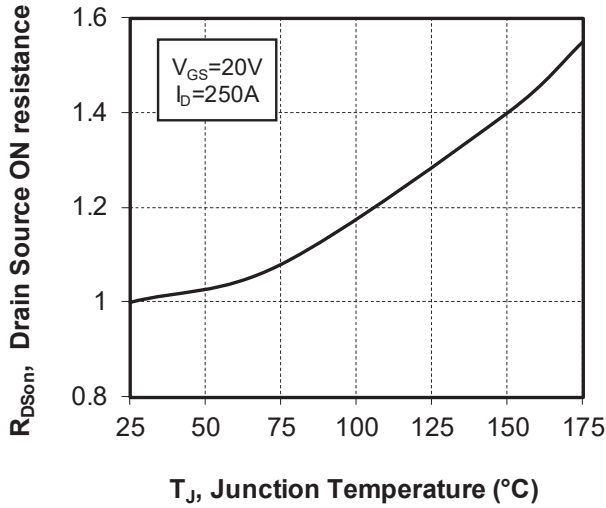


Figure 1-5. Transfer Characteristics

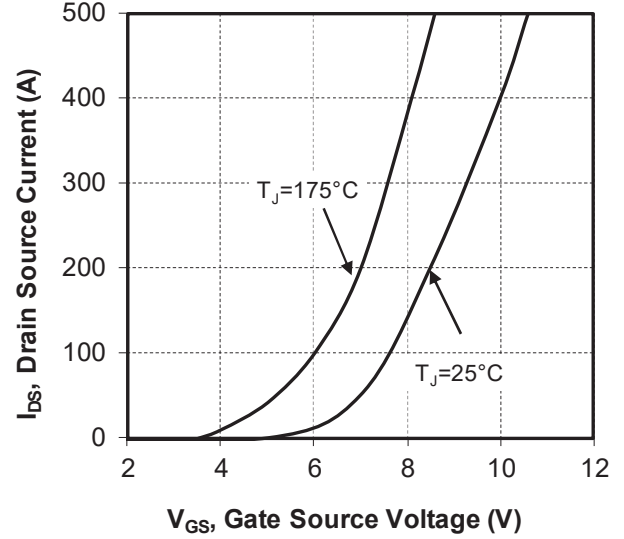


Figure 1-6. Switching Energy vs. R_g

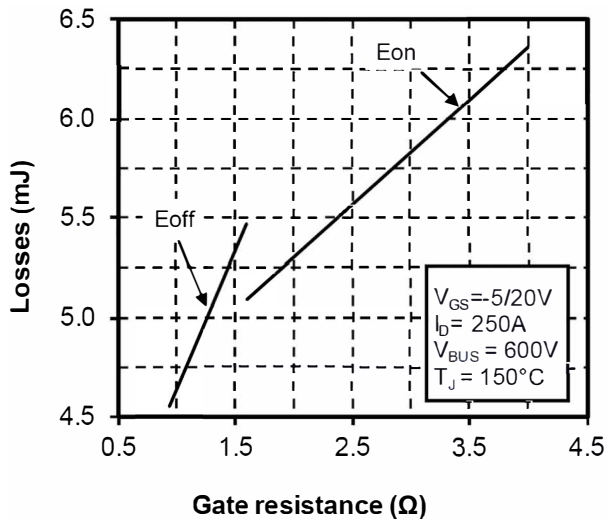


Figure 1-7. Switching Energy vs. Current

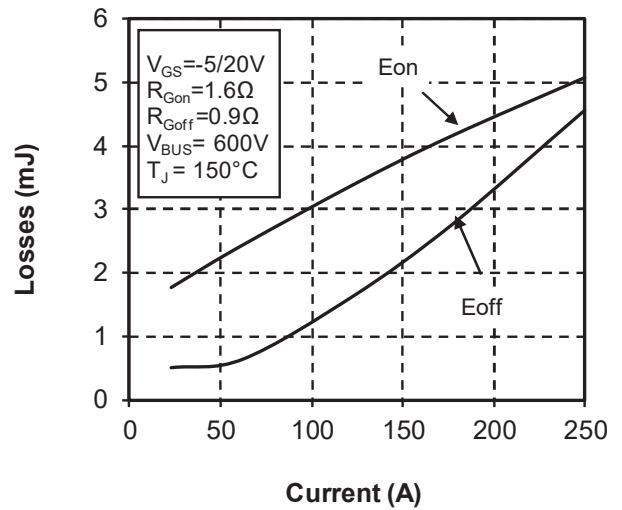


Figure 1-8. Capacitance vs. Drain Source Voltage

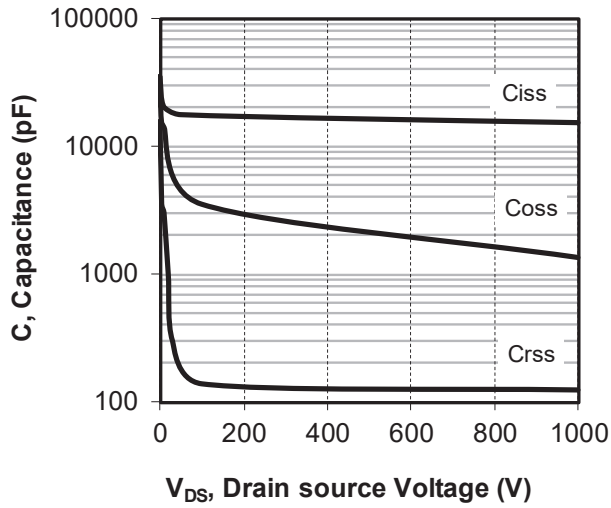


Figure 1-9. Gate Charge vs. Gate Source Voltage

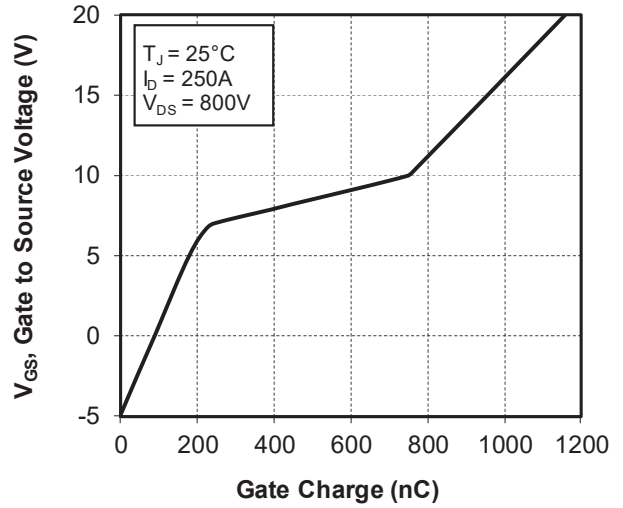


Figure 1-10. Body Diode Characteristics, $T_J = 25^\circ\text{C}$

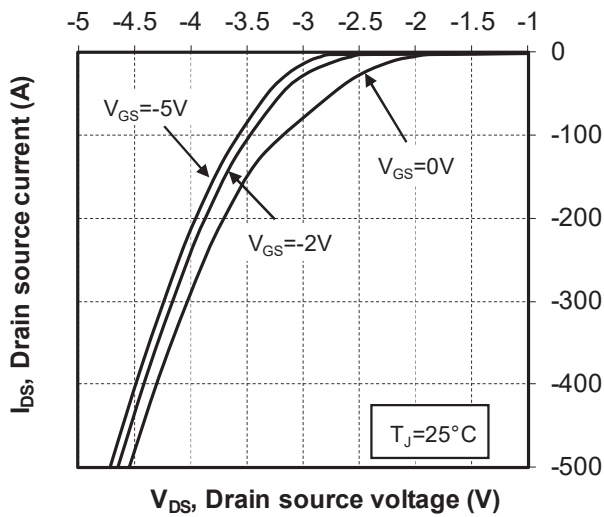


Figure 1-11. 3rd Quadrant Characteristics, $T_J = 25^\circ\text{C}$

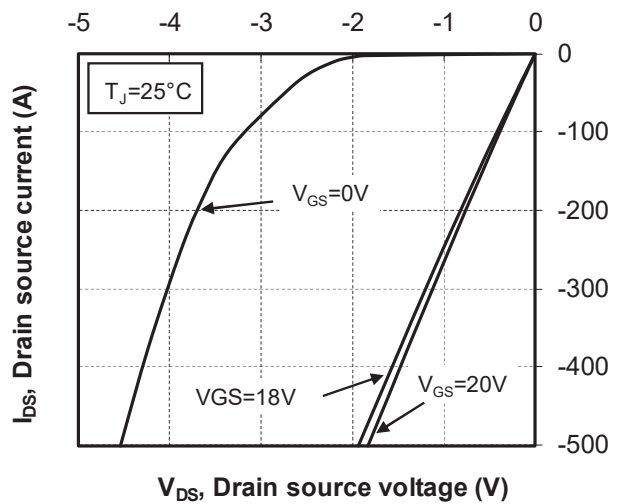


Figure 1-12. Body Diode Characteristics, $T_J = 175^\circ\text{C}$

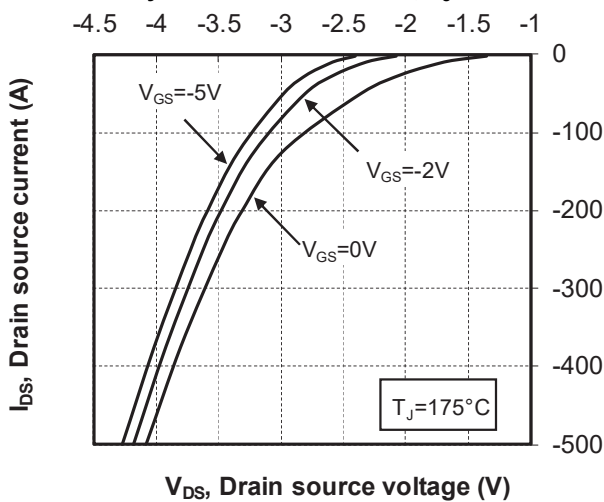


Figure 1-13. 3rd Quadrant Characteristics, $T_J = 175^\circ\text{C}$

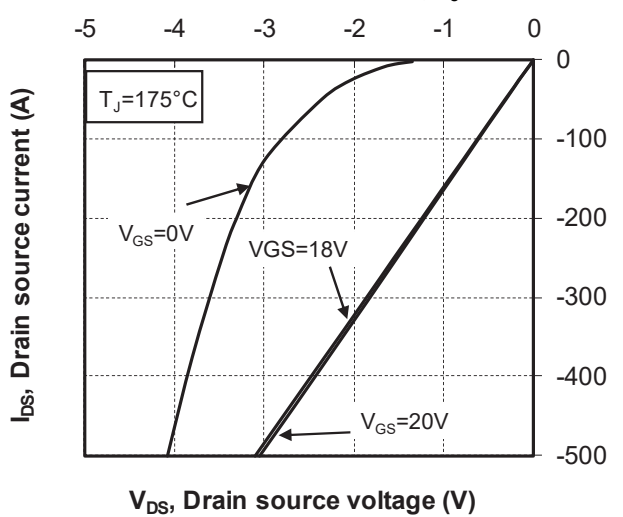
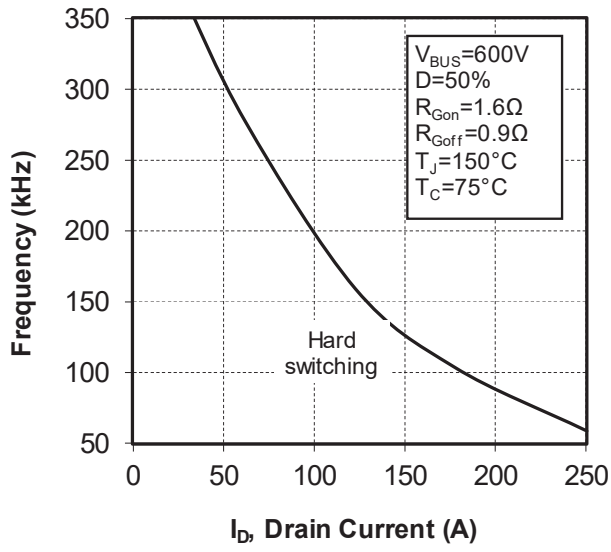


Figure 1-14. Operating Frequency vs. Drain Current



1.5 Typical SiC Diode Performance Curve

The following figures show the SiC diode performance curves of the MSCSM120VR1M062CT6AG device.

Figure 1-15. Maximum Thermal Impedance

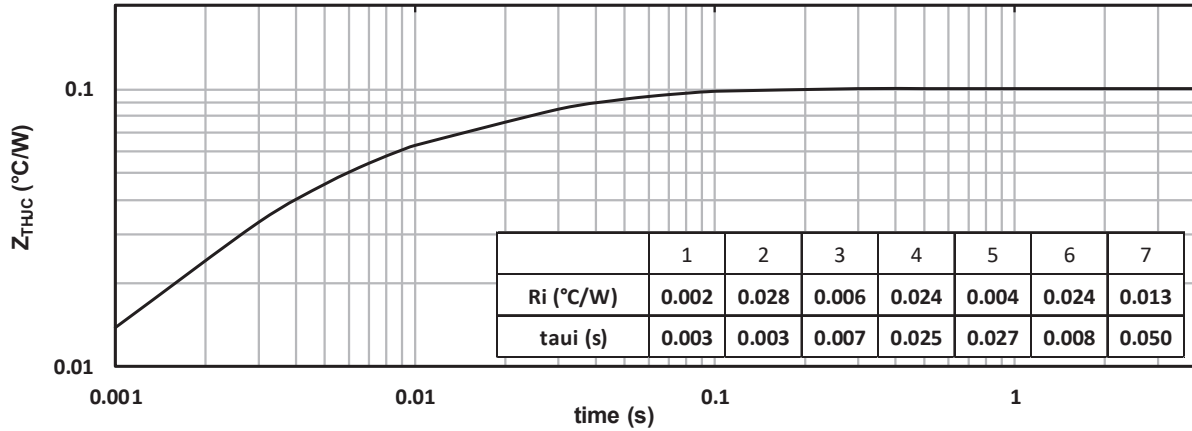


Figure 1-16. Forward Characteristics

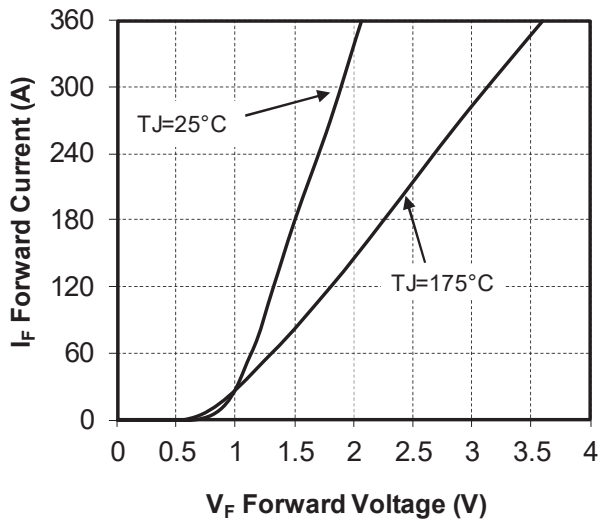
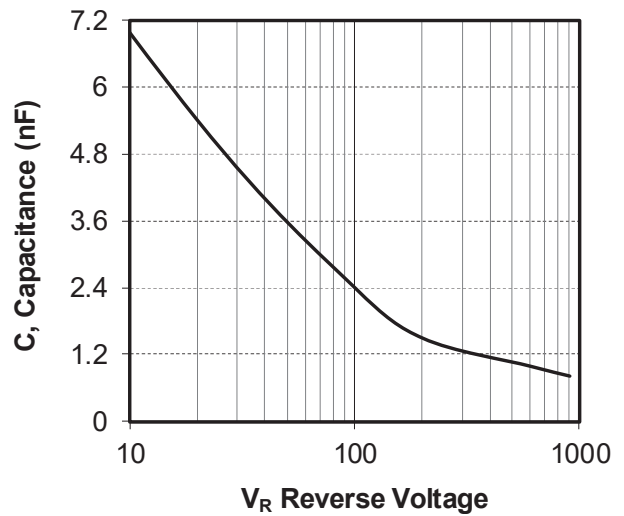


Figure 1-17. Capacitance vs. Reverse Voltage



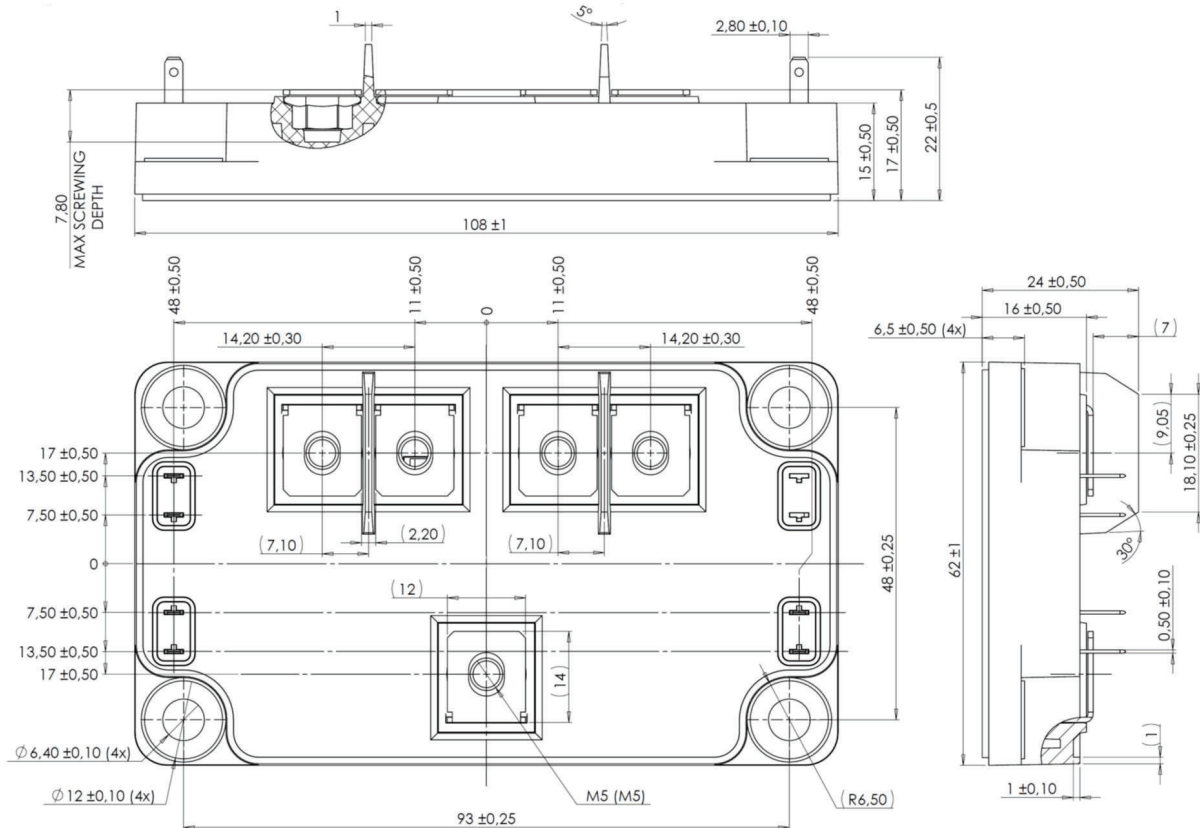
2. Package Specifications

The following section shows the package specification of the MSCSM120VR1M062CT6AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120VR1M062CT6AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



3. Revision History

Revision	Date	Description
A	08/2022	Initial Revision

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